

TCO08URU

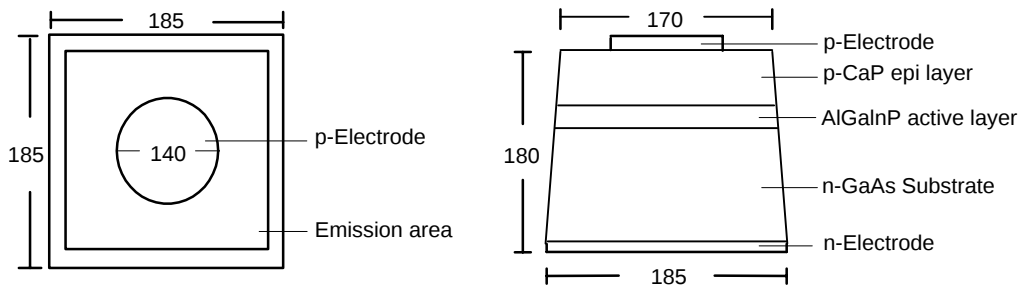
■ Features :

- MOVPE epi wafer
- Low cost

■ Typical Applications :

- Lamp

■ Outline Dimensions : (Unit: μm)



■ Physical Structure :

Chip dimension	Chip size	185 μm x 185 μm
	Thickness	180 μm
	Emission area	170 μm
	Bonding pad	140 μm
Electrode	Top: P (anode)	Aluminum (Gold optional)
	Backside: N (cathode)	Gold alloy
Surface condition	Not frosted	

■ Electro-Optical Characteristics : ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20 \text{ mA}$	-	1.90	2.40	V
Reverse Voltage	V_R	$I_R = 10 \mu\text{A}$	5	-	-	V
Wavelength	λ_p	$I_F = 20 \text{ mA}$	-	638	-	nm
	λ_D		615	625	635	
Spectral width at half height	$\Delta\lambda$	$I_F = 20 \text{ mA}$	-	20	-	nm
Luminous Intensity	I_v	B	20	-	-	mcd
		C	30	-	-	
		D	40	-	-	